

Appl. No. : 10/781,247
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AMENDMENTS TO THE SPECIFICATION

Please amend the Specification as follows. Insertions are shown underlined while deletions are shown in [[double brackets]].

Page 9, paragraph [0044]:

With its flow rate controlled at a given value by a mass flow controller (not shown), a reaction gas used for depositing a film onto the semiconductor substrate 4 is introduced into the reactor 2 from a port 19 via piping 15, a valve 13, inlet piping 14 and an opening 17. The reaction gas flowing in from the opening 17 is fed into the showerhead 5 and to the upper surface of the semiconductor substrate 4 through thousands of fine pores (not shown) provided in a surface of the showerhead 5 facing the semiconductor substrate 4. To deposit a film onto the semiconductor substrate 4 by decomposing the reaction gas, a radio-frequency power generator 10 is connected to the showerhead 5 via a radio-frequency power matching circuit [[10]]2. Plasma discharge is formed between the showerhead 5 and the susceptor heater 3 supporting the semiconductor substrate 4.